

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VLB70-12F is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|--------------------------------|
| I_C | 12 A |
| V_{CB0} | 36 V |
| V_{CEO} | 18 V |
| V_{EBO} | 3.5 V |
| P_{DISS} | 183 W @ T _C = 25 °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 1.05 °C/W |

PACKAGE STYLE .380 4L FLG

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .785 / 19.94 | |
| C | .720 / 18.29 | .730 / 18.54 |
| D | .970 / 24.64 | .980 / 24.89 |
| E | | .385 / 9.78 |
| F | .004 / 0.10 | .006 / 0.15 |
| G | .085 / 2.16 | .105 / 2.67 |
| H | .160 / 4.06 | .180 / 4.57 |
| I | | .280 / 7.11 |
| J | .240 / 6.10 | .255 / 6.48 |

ORDER CODE: ASI10737

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|--|---|---------|---------|---------|-----------------------|
| BV_{CB0} | I _C = 50 mA | 36 | | | V |
| BV_{CES} | I _C = 100 mA | 36 | | | V |
| BV_{CEO} | I _C = 50 mA | 18 | | | V |
| BV_{EBO} | I _E = 10 mA | 3.5 | | | V |
| I_{CES} | V _{CE} = 15 V | | | 10 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 5.0 A | 10 | | --- | --- |
| C_{OB} | V _{CB} = 12.5 V MHz f = 1.0 | | | 270 | pF |
| G_P η_C | V _{CE} = 12.5 V P _{OUT} = 70 W f = 50 MHz | 10 | 60 | | dB % |